Ke Zou

List of Publications by Year
in descending order

34 papers	1,883 citations	430874 18 h-index	395702 33 g-index
35 all docs	35 docs citations	35 times ranked	3374 citing authors

#	Article	IF	Citations
1	Electronic properties of epitaxial La1â^'xSrxRhO3 thin films. Physical Review B, 2021, 103, .	3.2	3
2	High-order replica bands in monolayer FeSe/SrTiO3 revealed by polarization-dependent photoemission spectroscopy. Nature Communications, 2021, 12, 4573.	12.8	11
3	Single-crystalline epitaxial TiO film: A metal and superconductor, similar to Ti metal. Science Advances, 2021, 7, .	10.3	14
4	High-temperature superconductivity and its robustness against magnetic polarization in monolayer FeSe on EuTiO3. Npj Quantum Materials, 2021, 6, .	5.2	14
5	Weak antilocalization in topological crystalline insulator SnTe films deposited using amorphous seeding on SrTiO3. APL Materials, 2021, 9, .	5.1	4
6	Robust ferromagnetism in wafer-scale monolayer and multilayer Fe3GeTe2. Npj 2D Materials and Applications, 2020, 4, .	7.9	37
7	Identifying crystal structures and chemical reactions at the interface of stanene on Bi2Te3. Journal of Applied Physics, 2020, 128, .	2.5	1
8	Controlling the electrical and magnetic ground states by doping in the complete phase diagram of titanate <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:msub><mml:mi>Eu</mml:mi><mml:mrow><mml:mn>1</mml:mn></mml:mrow></mml:msub></mml:mrow></mml:math> thin films. Physical Review B, 2020, 101, .	3.2	7
9	Tuning stoichiometry and its impact on superconductivity of monolayer and multilayer FeSe on <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>SrTi</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>. Physical Review B, 2020, 101, .	3.2	16
10	Picoscale structural insight into superconductivity of monolayer FeSe/SrTiO ₃. Science Advances, 2020, 6, eaay4517.	10.3	24
11	Revealing surface-state transport in ultrathin topological crystalline insulator SnTe films. APL Materials, 2019, 7, .	5.1	9
12	Epitaxial growth of perovskite <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>SrBiO</mml:mi><mml:mn>3</mml:mn></mml:msub></m film on <mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:msub><mml:mi>SrTiO</mml:mi><mml:mn>3</mml:mn></mml:msub></m by oxide molecular beam epitaxy. Physical Review Materials, 2019, 3, .	2.4	9
13	Suppression of the spectral weight of topological surface states on the nanoscale via local symmetry breaking. Physical Review Materials, 2018, 2, .	2.4	3
14	Length Scale and Dimensionality of Defects in Epitaxial SnTe Topological Crystalline Insulator Films. Advanced Materials Interfaces, 2017, 4, 1601011.	3.7	6
15	Crystalline Insulators: Length Scale and Dimensionality of Defects in Epitaxial SnTe Topological Crystalline Insulator Films (Adv. Mater. Interfaces 2/2017). Advanced Materials Interfaces, 2017, 4, .	3.7	1
16	Role of double<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>Ti</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:mrow></mml:math>layers at the interface of FeSe/<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>SrTi</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>superconductors.	3.2	40
17	Surface phase, morphology, and charge distribution transitions on vacuum and ambient annealed<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML"><mml:mrow><mml:mi>SrTi</mml:mi><mml:msub><mml:mi mathvariant="normal">O</mml:mi><mml:mn>3</mml:mn></mml:msub></mml:mrow></mml:math>(100). Physical Review B, 2016, 93, .	3.2	34
18	Effective mass in bilayer graphene at low carrier densities: The role of potential disorder and electron-electron interaction. Physical Review B, 2016, 94, .	3.2	16

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19	LaTiO3/KTaO3 interfaces: A new two-dimensional electron gas system. APL Materials, 2015, 3, .	5.1	94
20	A high density two-dimensional electron gas in an oxide heterostructure on Si (001). APL Materials, 2014, 2, 116109.	5.1	29
21	Transport Studies of Dual-Gated ABC and ABA Trilayer Graphene: Band Gap Opening and Band Structure Tuning in Very Large Perpendicular Electric Fields. Nano Letters, 2013, 13, 369-373.	9.1	109
22	HongetÂal.Reply:. Physical Review Letters, 2012, 109, .	7.8	3
23	Evidence for Spin-Flip Scattering and Local Moments in Dilute Fluorinated Graphene. Physical Review Letters, 2012, 108, 226602.	7.8	115
24	Integrating functional oxides with graphene. Solid State Communications, 2012, 152, 1365-1374.	1.9	37
25	Multiferroic tunnel junctions. Frontiers of Physics, 2012, 7, 380-385.	5.0	41
26	Effective mass of electrons and holes in bilayer graphene: Electron-hole asymmetry and electron-electron interaction. Physical Review B, 2011, 84, .	3.2	104
27	Mechanism for Current Saturation and Energy Dissipation in Graphene Transistors. Physical Review Letters, 2010, 104, 236601.	7.8	76
28	Unusual resistance hysteresis in n-layer graphene field effect transistors fabricated on ferroelectric Pb(Zr0.2Ti0.8)O3. Applied Physics Letters, 2010, 97, .	3.3	115
29	Deposition of High-Quality<mml:math xmlns:mml="http://www.w3.org/1998/Math/MathML" display="inline"><mml:msub><mml:mi>HfO</mml:mi><mml:mn>2</mml:mn></mml:msub></mml:math>on Graphene and the Effect of Remote Oxide Phonon Scattering. Physical Review Letters, 2010, 105, 126601.	7.8	155
30	Reversible fluorination of graphene: Evidence of a two-dimensional wide bandgap semiconductor. Physical Review B, 2010, 81, .	3.2	365
31	Transport in gapped bilayer graphene: The role of potential fluctuations. Physical Review B, 2010, 82, .	3.2	85
32	Quantum scattering time and its implications on scattering sources in graphene. Physical Review B, 2009, 80, .	3.2	107
33	High-Mobility Few-Layer Graphene Field Effect Transistors Fabricated on Epitaxial Ferroelectric Gate Oxides. Physical Review Letters, 2009, 102, 136808.	7.8	197
34	Hydrogen Atom Dopingâ€"A Versatile Method for Modulated Interface Resistive Switching. Advanced Electronic Materials, 0, , 2200353.	5.1	2